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## NTE5810 & NTE5811, NTE5870 thru NTE5891 Silicon Power Rectifier Diode, 12 Amp, DO4

**Description:**

The NTE5810, NTE5811, and NTE5870 through NTE5891 are low power general purpose rectifier diodes in a DO4 type package designed for battery chargers, converters, power supplies, and machine tool controls.

**Features:**

- High Surge Current Capability
- High Voltage Available
- Designed for a Wide Range of Applications
- Available in Anode-to-Case or Cathode-to-Case Style

**Ratings and Characteristics:**

Average Forward Current ( $T_C = +144^\circ\text{C Max}$ ),  $I_{F(AV)}$  ..... 12A  
 Maximum Forward Surge Current,  $I_{FSM}$   
     50Hz ..... 230A  
     60Hz ..... 240A  
 Fusing Current,  $I^2t$   
     50Hz ..... 260A<sup>2</sup>s  
     60Hz ..... 240A<sup>2</sup>s  
 Fusing Current,  $I^2\sqrt{t}$  ..... 3580A<sup>2</sup> $\sqrt{s}$   
 Maximum Reverse Recovery Voltage Range,  $V_{RRM}$  ..... 50 to 1200V

**Voltage Ratings:** ( $T_J = +175^\circ\text{C}$ )

NTE Type Number		$V_{RRM}$ -Max Repetitive Peak Reverse Volt. (V)	$V_{RSM}$ -Max Non-Replicative Peak Reverse Voltage (V)	$V_R$ -Max. Direct Reverse Voltage (V)	$V_{R(SR)}$ Minimum Avalanche Voltage (V)	$I_{RM}$ -Max Reverse Current Rated $V_{RRM}$ (mA)
Cathode to Case	Anode to Case					
5870	5871	50	75	50	-	12
5872	5873	100	150	100	-	12
5874	5875	200	275	200	-	12
5876	5877	300	385	300	-	12
5878	5879	400	500	400	500	12
5880	5881	500	613	50	626	12
5882	5883	600	725	600	750	12
5886	5887	800	950	800	950	12
5890	5891	1000	1200	1000	1150	12
5810	5811	1200	1400	1200	1350	12

### Electrical Specifications:

Parameter	Symbol	Test Conditions		Rating	Unit
Maximum Average Forward Current	$I_F (AV)$	180° sinusoidal condition, $T_C = +144^\circ\text{C}$ Max		12	A
Maximum RMS Forward Current	$I_F (RMS)$			19	A
Maximum Peak One-Cycle Non-Repetitive Surge Current	$I_{FSM}$	$t = 10\text{ms}$	Sinusoidal Half Wave, No voltage reapplied	225	A
		$t = 8.3\text{ms}$		235	A
		$t = 10\text{ms}$	100% rated voltage reapplied, $T_J = +175^\circ\text{C}$	265	A
		$t = 8.3\text{ms}$		280	A
Maximum $I^2t$ for Individual Device Fusing	$I^2t$	$t = 10\text{ms}$	100% rated voltage reapplied, Initial $T_J = +175^\circ\text{C}$	351	$\text{A}^2\text{s}$
		$t = 8.3\text{ms}$		320	$\text{A}^2\text{s}$
Maximum $I^2\sqrt{t}$	$I^2\sqrt{t}$	$t = 0.1$ to $10\text{ms}$ , No voltage reapplied, Note 1		3511	$\text{A}^2\sqrt{t}$
Maximum Peak Forward Voltage	$V_{FM}$	$I_{FM} = 38\text{A}$ , $T_J = +25^\circ\text{C}$		1.26	V
Maximum Value of Threshold Voltage	$V_M (TO)$	$T_J = +175^\circ\text{C}$		0.68	V
Maximum Value of Forward Slope Resistance	$r_t$	$T_J = +175^\circ\text{C}$		13.51	$\text{m}\Omega$

Note 1.  $I^2t$  for time  $t_x = I^2\sqrt{t} \cdot \sqrt{t_x}$

### Thermal-Mechanical Specifications:

Parameter	Symbol	Test Conditions	Rating	Unit
Maximum Operation Junction Temperature	$T_J$		-65 to + 175	$^\circ\text{C}$
Maximum Storage Temperature	$T_{stg}$		-65 to + 200	$^\circ\text{C}$
Maximum Internal Thermal Resistance Junction-to-Case	$R_{thJC}$	DC operation	2.0	K/W
Thermal Resistance, Case-to-Sink	$R_{thCS}$	Mounting surface flat, smooth and greased	0.5	K/W
Mounting Torque	T	Non-lubricated threads	1.2 - 1.5 (10.5 - 13.5)	$\text{m}\cdot\text{N}$ ( $\text{in}\cdot\text{lb}$ )
Approximate Weight	wt		11 (0.25)	g (oz)

